

Title: "Semiconductor Heterostructures Having  
Reduced Dislocation Pile-Ups and Related Methods"  
Inventors: Westhoff *et al.*  
Serial No. 10/646,353  
Atty Docket No. ASC-058B  
Agent: Matthew T. Currie  
Replacement Sheet 1 of 6

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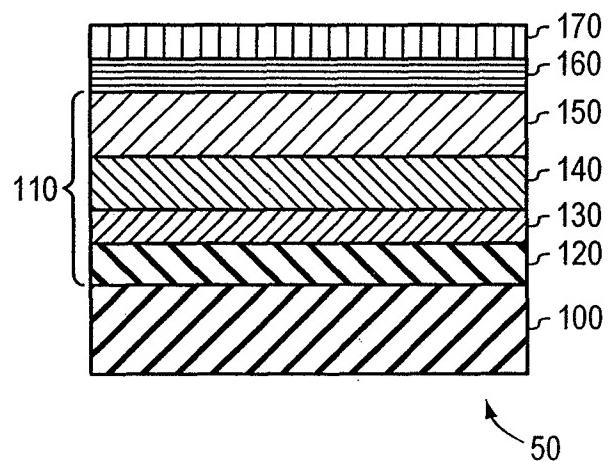


FIG. 1

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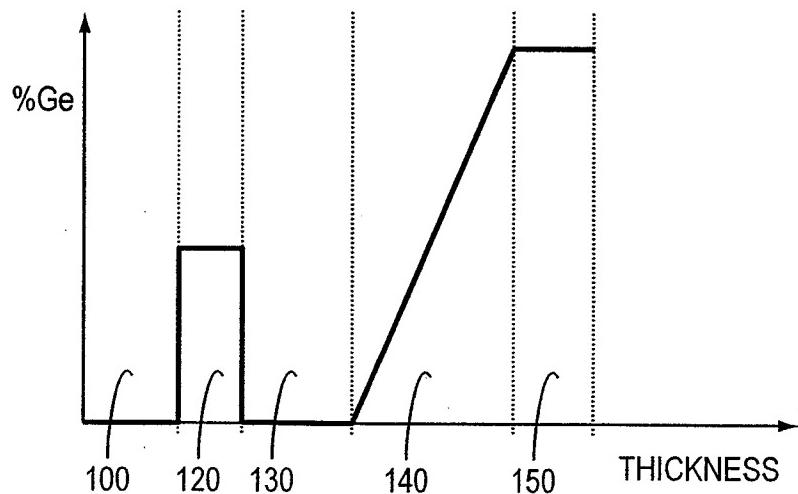


FIG. 2

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		QUALITATIVE EVALUATION OF DISLOCATION PILE-UP DENSITY			
% Ge	H* = 0.6 T <sub>crit</sub>	H = 1.25 T <sub>crit</sub>	H = 2 T <sub>crit</sub>	H = 5 T <sub>crit</sub>	
5	HIGH	MEDIUM	LOW	LOW	
10	HIGH	MEDIUM	MEDIUM	LOW	
15	HIGH	MEDIUM	MEDIUM	LOW	

\* THICKNESS (H) OF THE SEED LAYER RELATIVE  
TO ITS CRITICAL THICKNESS (T<sub>crit</sub>).

FIG. 3

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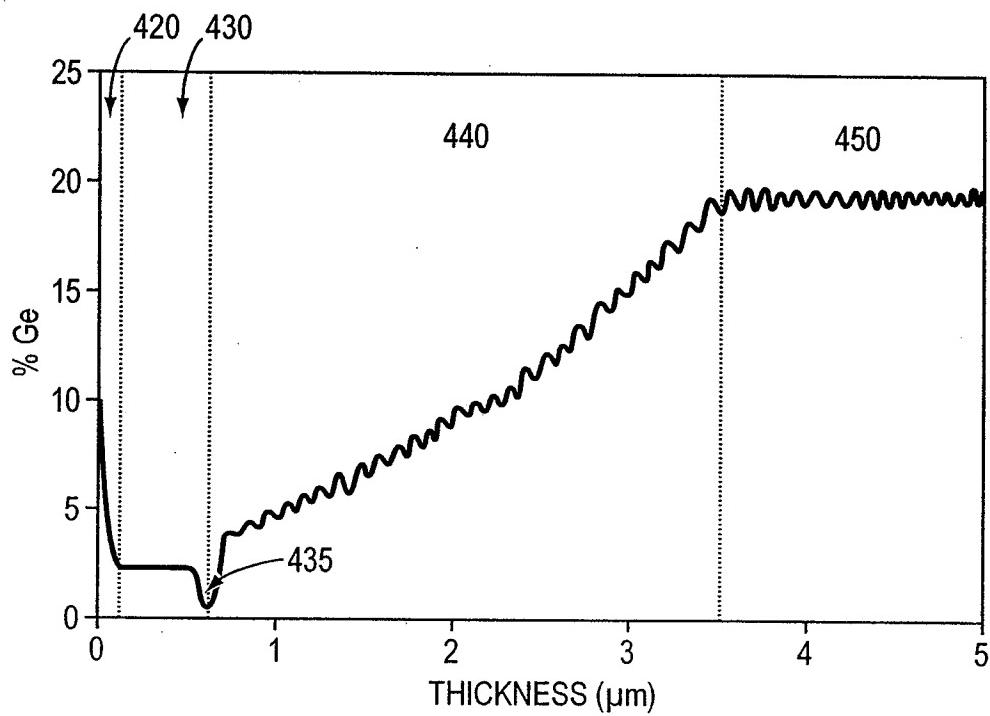


FIG. 4

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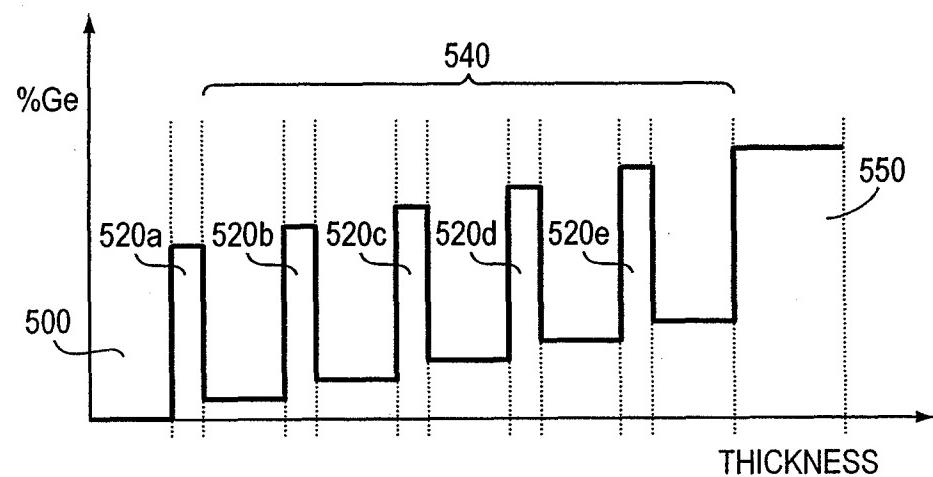


FIG. 5

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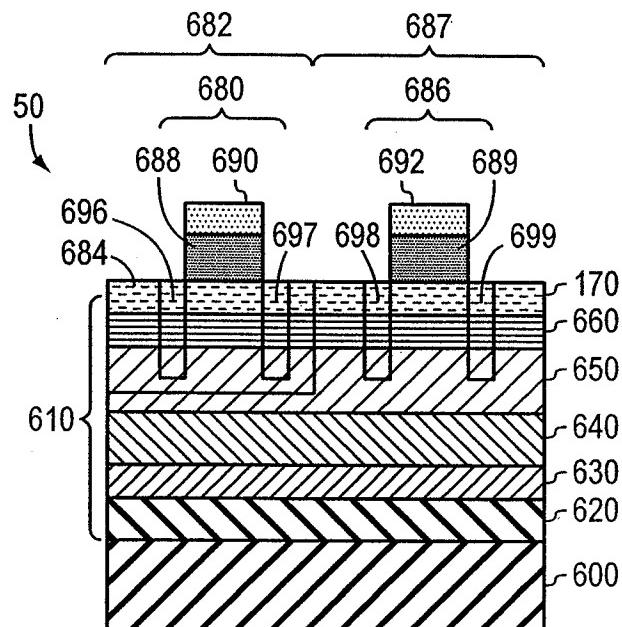


FIG. 6